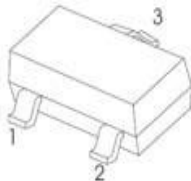
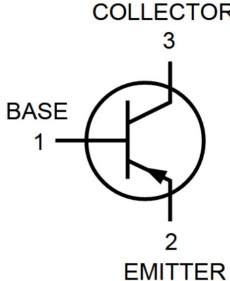
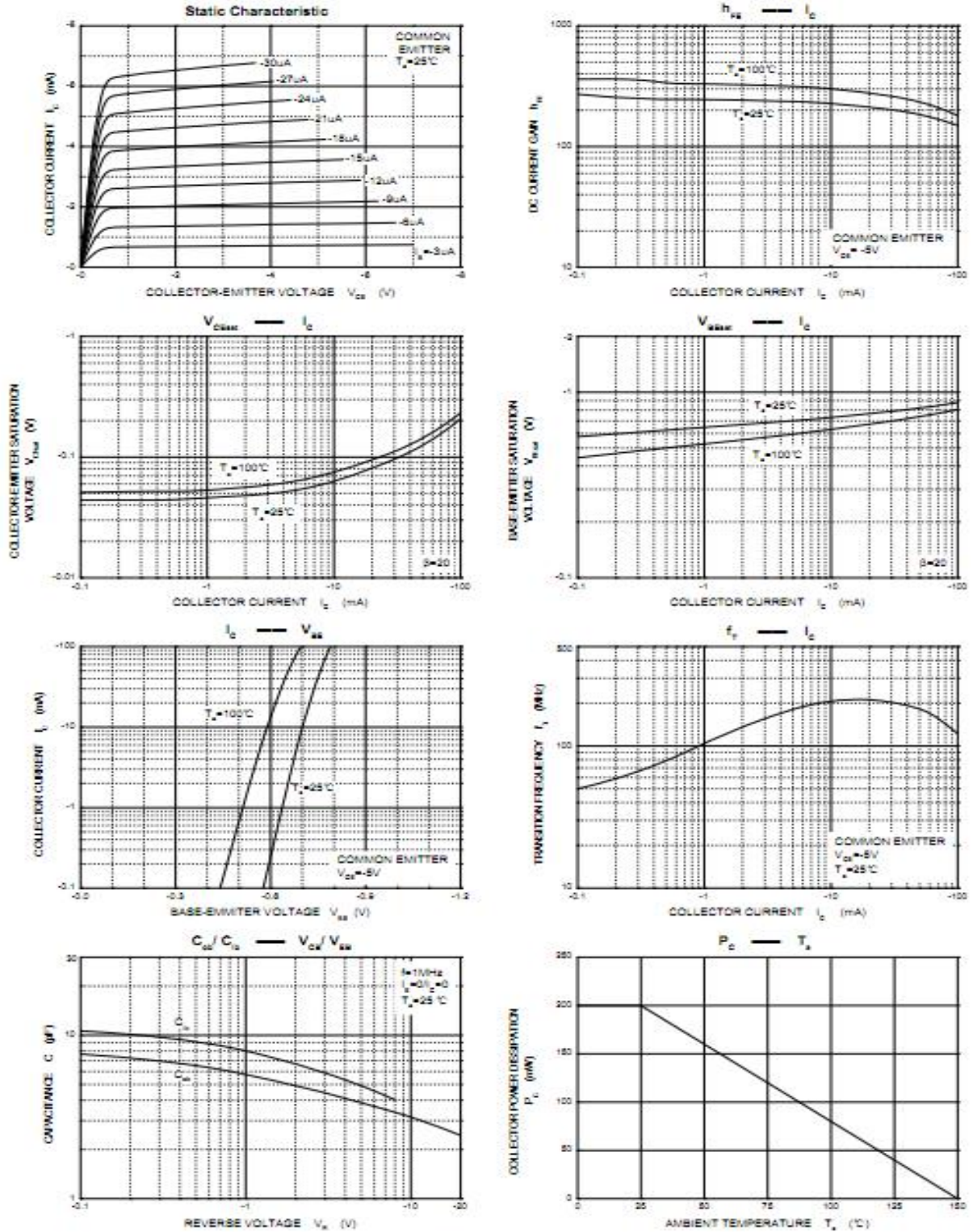


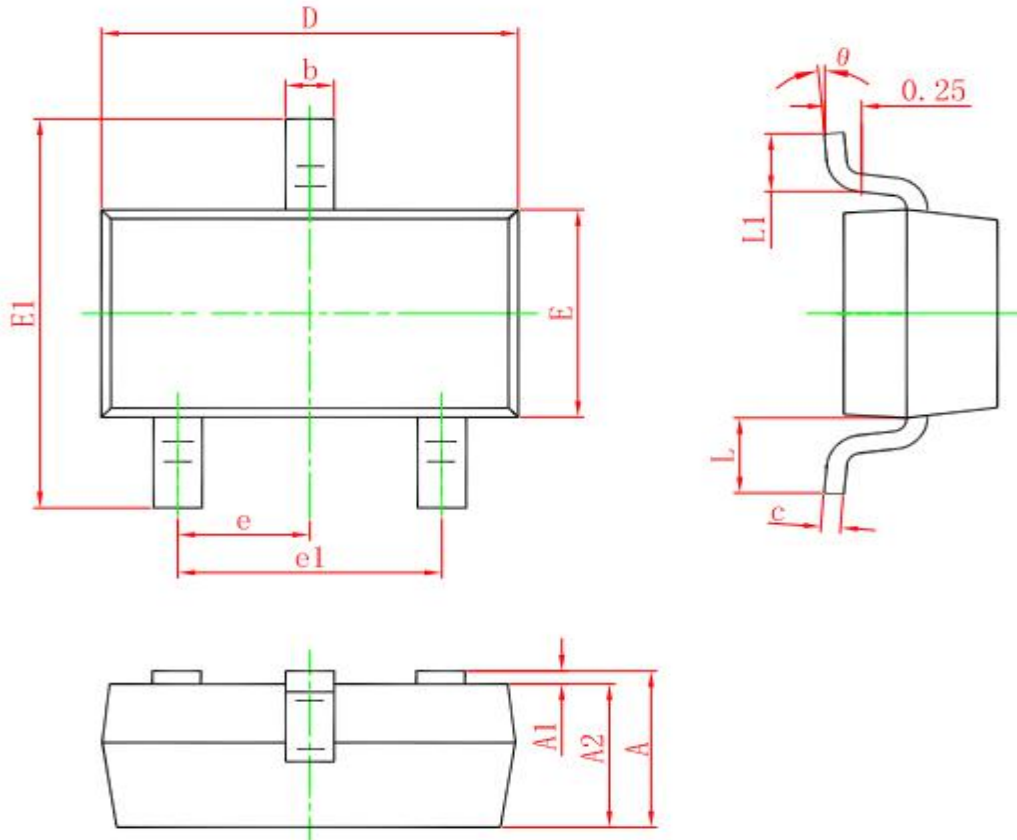
TRANSISTOR (PNP)		SOT-23 Plastic-Encapsulate Transistors						
<p><u>SOT-23</u></p>  <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Equivalent Circuit:</p> 		<p>Features</p> <ul style="list-style-type: none"> ※ Ideally suited for automatic insertion ※ For switching and AF amplifier applications 						
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)								
Parameter	Symbol	Value	Unit					
Collector-Base Voltage	VCBO	BC856 BC857 BC858	-80 -50 -30	V				
Collector-Emitter Voltage		VCEO	BC856 BC857 BC858	-65 -45 -30	V			
Emitter-Base Voltage			VEBO	-5	V			
Collector Current	IC		-0.1	A				
Collector Power Dissipation	PC	200	mW					
Thermal Resistance From Junction To Ambient	ROJA	625	°C/W					
Junction Temperature	Tj	150	°C					
Storage Temperature	Tstg	-65~+150	°C					
<table border="1"> <tr> <td>DEVICE MARKING:</td> </tr> <tr> <td>BC856A=3A; BC856B=3B</td> </tr> </table>		DEVICE MARKING:	BC856A=3A; BC856B=3B	<table border="1"> <tr> <td>BC857A=3E; BC857B=3F; BC857C=3G</td> </tr> <tr> <td>BC858A=3J; BC858B=3K; BC858C=3L</td> </tr> </table>			BC857A=3E; BC857B=3F; BC857C=3G	BC858A=3J; BC858B=3K; BC858C=3L
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ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage BC856 BC857 BC858	V(BR)CBO	IC= -10µA, IE=0	-80 -50 -30			V
Collector-emitter breakdown voltage BC856 BC857 BC858	V(BR)CEO	IC= -10mA, IB=0	-65 -45 -30			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-1µA, IC=0	-5			V
Collector cut-off current BC856 BC857 BC858	ICBO	VCB=-70 V , IE=0 VCB=-50 V , IE=0 VCB=-30 V , IE=0			-0.1	µA
Emitter cut-off current	IEBO	VEB=-5V , IC=0			-0.1	µA
DC current gain BC856A; 845A; 858A BC856B; 857B; 858B BC857C; BC858C	hFE	VCE=-5V, IC= -2mA	125 220 420		250 475 800	
Collector-emitter saturation voltage	VCE(sat)	IC=-100 mA, IB= -5mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=-100 mA, IB= -5mA			-1.1	V
Transition frequency	fT	VCE=-5V, IC= -10mA f=100MHz	100			MHz
Collector Current Capacitance	Cob	VCE=-10V, f=1MHz			4.5	pF
CLASSIFICATION OF hFE						
Rank	L	H	J			
Range	125-200	200-350	300-400			

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)